

isc N-Channel MOSFET Transistor

IPB65R110CFD

• FEATURES

- With TO-263(D2PAK) packaging
- Ultra-fast body diode
- High speed switching
- Very high commutation ruggedness
- Easy to use
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operationz

• APPLICATIONS

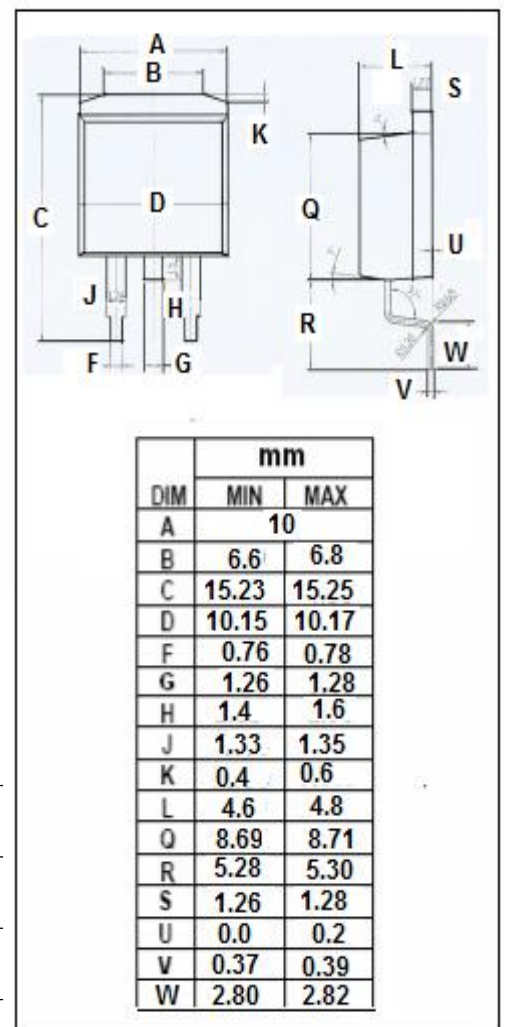
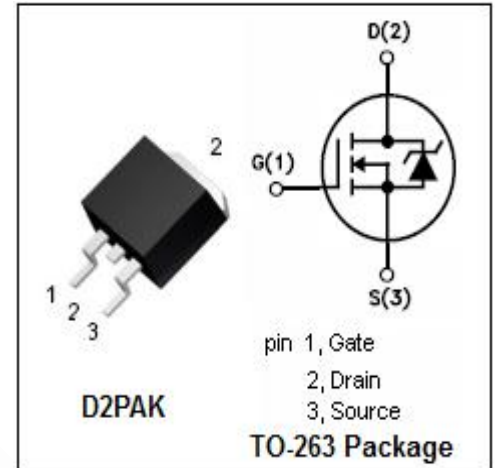
- Switching applications

• ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DS}	Drain-Source Voltage	650	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-Continuous@ $T_c=25^{\circ}\text{C}$ $T_c=100^{\circ}\text{C}$	31.2 19.7	A
I_{DM}	Drain Current-Single Pulsed	99.6	A
P_D	Total Dissipation	277.8	W
T_j	Operating Junction Temperature	-55~150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~150	$^{\circ}\text{C}$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	0.45	$^{\circ}\text{C/W}$
$R_{th(ch-a)}$	Channel-to-ambient thermal resistance	62	$^{\circ}\text{C/W}$



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ELECTRICAL CHARACTERISTICS

 $T_c=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DS}	Drain-Source Breakdown Voltage	$V_{GS}=0V; I_D=1mA$	650			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=\pm 20V; I_D=1.3mA$	3.5		4.5	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V; I_D=12.7A$		99	110	$m\Omega$
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V; V_{DS}=0V$			± 0.1	μA
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=650V; V_{GS}=0V @ T_c=25^{\circ}\text{C}$ $T_c=125^{\circ}\text{C}$			1.5 400	μA
V_{SDF}	Diode forward voltage	$I_{SD}=19.1A, V_{GS}=0V$			0.9	V